Kazuhito Tsukagoshi

List of Publications by Citations

348 papers	12,094 citations	59 h-index	97 g-index
381 ext. papers	13,152 ext. citations	5.2 avg, IF	6.28 L-index

#	Paper	IF	Citations
348	Coherent transport of electron spin in a ferromagnetically contacted carbon nanotube. *Nature*, **1999**, 401, 572-574	50.4	686
347	Solution-processable organic single crystals with bandlike transport in field-effect transistors. *Advanced Materials*, **2011**, 23, 523-6	24	333
346	Charge transport and mobility engineering in two-dimensional transition metal chalcogenide semiconductors. *Chemical Society Reviews*, **2016**, 45, 118-51	58.5	311
345	Ambipolar MoTe2 transistors and their applications in logic circuits. *Advanced Materials*, **2014**, 26, 3263-9	24	308
344	Quantitative Raman spectrum and reliable thickness identification for atomic layers on insulating substrates. *ACS Nano*, **2012**, 6, 7381-8	16.7	274
343	Simple and scalable gel-based separation of metallic and semiconducting carbon nanotubes. *Nano Letters*, **2009**, 9, 1497-500	11.5	272
342	Low-cost fully transparent ultraviolet photodetectors based on electrospun ZnO-SnO2 heterojunction nanofibers. *Advanced Materials*, **2013**, 25, 4625-30	24	243
341	Thickness-dependent interfacial Coulomb scattering in atomically thin field-effect transistors. *Nano Letters*, **2013**, 13, 3546-52	11.5	236
340	High-performance top-gated monolayer SnS2 field-effect transistors and their integrated logic circuits. *Nanoscale*, **2013**, 5, 9666-70	7.7	226
339	Strong enhancement of Raman scattering from a bulk-inactive vibrational mode in few-layer MoTe *ACS Nano*, **2014**, 8, 3895-903	16.7	223
338	Direct evaluation of low-field mobility and access resistance in pentacene field-effect transistors. *Journal of Applied Physics*, **2010**, 107, 114507	2.5	159
337	Self-limiting layer-by-layer oxidation of atomically thin WSe2. *Nano Letters*, **2015**, 15, 2067-73	11.5	153
336	Improvement of subthreshold current transport by contact interface modification in p-type organic field-effect transistors. *Applied Physics Letters*, **2009**, 94, 143304	3.4	152
335	In-crystal and surface charge transport of electric-field-induced carriers in organic single-crystal semiconductors. *Physical Review Letters*, **2007**, 98, 196804	7.4	150
334	Ambipolar-transporting coaxial nanotubes with a tailored molecular graphene-fullerene heterojunction. *Proceedings of the National Academy of Sciences of the United States of America*, **2009**, 106, 21051-6	11.5	149
333	Origin of the relatively low transport mobility of graphene grown through chemical vapor deposition. *Scientific Reports*, **2012**, 2, 337	4.9	148
332	Hall Effect of Quasi-Hole Gas in Organic Single-Crystal Transistors. *Japanese Journal of Applied Physics*, **2005**, 44, L1393-L1396	1.4	143

331	Charge injection process in organic field-effect transistors. *Applied Physics Letters*, **2007**, 91, 053508	3.4	132
330	Thickness scaling effect on interfacial barrier and electrical contact to two-dimensional MoS2 layers. *ACS Nano*, **2014**, 8, 12836-42	16.7	129
329	Contact-metal dependent current injection in pentacene thin-film transistors. *Applied Physics Letters*, **2007**, 91, 203508	3.4	125
328	Evaluation of Spin Hall Angle and Spin Diffusion Length by Using Spin Current-Induced Ferromagnetic Resonance. *Applied Physics Express*, **2012**, 5, 073002	2.4	121
327	Modification of the electric conduction at the pentacene□SiO2 interface by surface termination of SiO2. *Applied Physics Letters*, **2005**, 86, 103502	3.4	119
326	Carbon nanotube devices for nanoelectronics. *Physica B: Condensed Matter*, **2002**, 323, 107-114	2.8	116
325	Highly enhanced charge injection in thienoacene-based organic field-effect transistors with chemically doped contact. *Applied Physics Letters*, **2012**, 100, 093303	3.4	115
324	High-performance transparent flexible transistors using carbon nanotube films. *Applied Physics Letters*, **2006**, 88, 033511	3.4	112
323	Influence of disorder on conductance in bilayer graphene under perpendicular electric field. *Nano Letters*, **2010**, 10, 3888-92	11.5	106
322	Direct observation of contact and channel resistance in pentacene four-terminal thin-film transistor patterned by laser ablation method. *Applied Physics Letters*, **2004**, 84, 813-815	3.4	102
321	Controlled self-assembly of organic semiconductors for solution-based fabrication of organic field-effect transistors. *Advanced Materials*, **2012**, 24, 299-306	24	96
320	Low operating bias and matched input-output characteristics in graphene logic inverters. *Nano Letters*, **2010**, 10, 2357-62	11.5	94
319	Self-Limiting Oxides on WSe2 as Controlled Surface Acceptors and Low-Resistance Hole Contacts. *Nano Letters*, **2016**, 16, 2720-7	11.5	90
318	Electrostatically Reversible Polarity of Ambipolar □MoTe2 Transistors. *ACS Nano*, **2015**, 9, 5976-83	16.7	89
317	Introducing Nonuniform Strain to Graphene Using Dielectric Nanopillars. *Applied Physics Express*, **2011**, 4, 075102	2.4	89
316	Effects of dopants in InOx-based amorphous oxide semiconductors for thin-film transistor applications. *Applied Physics Letters*, **2013**, 103, 172105	3.4	88
315	Correlation between grain size and device parameters in pentacene thin film transistors. *Applied Physics Letters*, **2008**, 93, 043311	3.4	87
314	Surface selective deposition of molecular semiconductors for solution-based integration of organic field-effect transistors. *Applied Physics Letters*, **2009**, 94, 093307	3.4	86

313	High-density electrostatic carrier doping in organic single-crystal transistors with polymer gel electrolyte. *Applied Physics Letters*, **2006**, 88, 112102	3.4	86
312	Flexible SnO(2) hollow nanosphere film based high-performance ultraviolet photodetector. *Chemical Communications*, **2013**, 49, 3739-41	5.8	85
311	Control of Carrier Density by a Solution Method in Carbon-Nanotube Devices. *Advanced Materials*, **2005**, 17, 2430-2434	24	82
310	Bias stress instability in pentacene thin film transistors: Contact resistance change and channel threshold voltage shift. *Applied Physics Letters*, **2008**, 92, 063305	3.4	81
309	Solution-processed, Self-organized Organic Single Crystal Arrays with Controlled Crystal Orientation. *Scientific Reports*, **2012**, 2, 393	4.9	80
308	Double resonance Raman modes in monolayer and few-layer MoTe2. *Physical Review B*, **2015**, 91,	3.3	76
307	Polarization measurements in tip-enhanced Raman spectroscopy applied to single-walled carbon nanotubes. *Chemical Physics Letters*, **2005**, 410, 136-141	2.5	73
306	Selective organization of solution-processed organic field-effect transistors. *Applied Physics Letters*, **2008**, 92, 173301	3.4	72
305	Determination of the Number of Graphene Layers: Discrete Distribution of the Secondary Electron Intensity Stemming from Individual Graphene Layers. *Applied Physics Express*, **2010**, 3, 095101	2.4	71
304	Charge trapping induced current instability in pentacene thin film transistors: Trapping barrier and effect of surface treatment. *Applied Physics Letters*, **2008**, 93, 033304	3.4	71
303	Stable amorphous In2O3-based thin-film transistors by incorporating SiO2 to suppress oxygen vacancies. *Applied Physics Letters*, **2014**, 104, 102103	3.4	70
302	Inter-Layer Screening Length to Electric Field in Thin Graphite Film. *Applied Physics Express*, **2008**, 1, 034007	2.4	70
301	Site-Selection in Single-Molecule Junction for Highly Reproducible Molecular Electronics. *Journal of the American Chemical Society*, **2016**, 138, 1294-300	16.4	69
300	Conduction tuning of graphene based on defect-induced localization. *ACS Nano*, **2013**, 7, 5694-700	16.7	69
299	Spin-dependent boundary resistance in the lateral spin-valve structure. *Applied Physics Letters*, **2004**, 85, 3501-3503	3.4	69
298	Understanding contact behavior in organic thin film transistors. *Applied Physics Letters*, **2010**, 97, 063307	3.4	68
297	Low-temperature processable amorphous In-W-O thin-film transistors with high mobility and stability. *Applied Physics Letters*, **2014**, 104, 152103	3.4	67
296	Gate control of spin transport in multilayer graphene. *Applied Physics Letters*, **2008**, 92, 212110	3.4	67

295	Direct observation of the electronic states of single crystalline rubrene under ambient condition by photoelectron yield spectroscopy. *Applied Physics Letters*, **2008**, 93, 173305	3.4	67
294	Large plate-like organic crystals from direct spin-coating for solution-processed field-effect transistor arrays with high uniformity. *Organic Electronics*, **2012**, 13, 264-272	3.5	65
293	Epitaxial Growth and Electronic Properties of Large Hexagonal Graphene Domains on Cu(111) Thin Film. *Applied Physics Express*, **2013**, 6, 075101	2.4	65
292	Strain-induced superconductor/insulator transition and field effect in a thin single crystal of molecular conductor. *Applied Physics Letters*, **2008**, 92, 243508	3.4	61
291	Suppression of thermally activated carrier transport in atomically thin MoS2 on crystalline hexagonal boron nitride substrates. *Nanoscale*, **2013**, 5, 9572-6	7.7	60
290	Current transport in short channel top-contact pentacene field-effect transistors investigated with the selective molecular doping technique. *Applied Physics Letters*, **2007**, 90, 193507	3.4	60
289	On practical charge injection at the metal/organic semiconductor interface. *Scientific Reports*, **2013**, 3, 1026	4.9	59
288	Gate-voltage dependence of zero-bias anomalies in multiwall carbon nanotubes. *Physical Review Letters*, **2004**, 92, 036801	7.4	59
287	Solution-processed organic crystals for field-effect transistor arrays with smooth semiconductor/dielectric interface on paper substrates. *Organic Electronics*, **2012**, 13, 815-819	3.5	58
286	Origin of Noise in Layered MoTe Transistors and its Possible Use for Environmental Sensors. *Advanced Materials*, **2015**, 27, 6612-9	24	58
285	Boost up carrier mobility for ferroelectric organic transistor memory via buffering interfacial polarization fluctuation. *Scientific Reports*, **2014**, 4, 7227	4.9	57
284	Barrier inhomogeneities at vertically stacked graphene-based heterostructures. *Nanoscale*, **2014**, 6, 795-9	7.7	56
283	Thin-film transistors fabricated by low-temperature process based on Ga- and Zn-free amorphous oxide semiconductor. *Applied Physics Letters*, **2013**, 102, 102101	3.4	55
282	Direct formation of organic semiconducting single crystals by solvent vapor annealing on a polymer base film. *Journal of Materials Chemistry*, **2012**, 22, 8462		52
281	Proximity effect in a superconductor-metallofullerene-superconductor molecular junction. *Physical Review B*, **2005**, 72,	3.3	52
280	Carrier Polarity Control in MoTe2 Schottky Junctions Based on Weak Fermi-Level Pinning. *ACS Applied Materials & Interfaces*, **2016**, 8, 14732-9	9.5	52
279	Suppression of short channel effect in organic thin film transistors. *Applied Physics Letters*, **2007**, 91, 113508	3.4	51
278	Frequency response analysis of pentacene thin-film transistors with low impedance contact by interface molecular doping. *Applied Physics Letters*, **2007**, 91, 013512	3.4	49

277	Optimal Structure for High-Performance and Low-Contact-Resistance Organic Field-Effect Transistors Using Contact-Doped Coplanar and Pseudo-Staggered Device Architectures. *Advanced Functional Materials*, **2012**, 22, 4577-4583	15.6	48
276	Self-assembly of semiconductor/insulator interfaces in one-step spin-coating: a versatile approach for organic field-effect transistors. *Physical Chemistry Chemical Physics*, **2013**, 15, 7917-33	3.6	47
275	High-yield production of single-wall carbon nanotubes in nitrogen gas. *Chemical Physics Letters*, **2003**, 372, 45-50	2.5	47
274	Dopant selection for control of charge carrier density and mobility in amorphous indium oxide thin-film transistors: Comparison between Si- and W-dopants. *Applied Physics Letters*, **2015**, 106, 042106	3.4	45
273	Field-induced carrier delocalization in the strain-induced mott insulating state of an organic superconductor. *Physical Review Letters*, **2009**, 103, 116801	7.4	45
272	Reversible and Precisely Controllable p/n-Type Doping of MoTe Transistors through Electrothermal Doping. *Advanced Materials*, **2018**, 30, e1706995	24	44
271	Magnetotransport through disordered and anisotropic antidot lattices in GaAs/AlxGa1-xAs heterostructures. *Physical Review B*, **1995**, 52, 8344-8347	3.3	44
270	Patterning solution-processed organic single-crystal transistors with high device performance. *AIP Advances*, **2011**, 1, 022149	1.5	43
269	Structure and transport properties of the interface between CVD-grown graphene domains. *Nanoscale*, **2014**, 6, 7288-94	7.7	42
268	Carrier mobility in organic field-effect transistors. *Journal of Applied Physics*, **2011**, 110, 104513	2.5	42
267	A Reliable Method for Fabricating sub-10 nm Gap Junctions Without Using Electron Beam Lithography. *E-Journal of Surface Science and Nanotechnology*, **2003**, 1, 41-44	0.7	42
266	Pentacene nanotransistor with carbon nanotube electrodes. *Applied Physics Letters*, **2004**, 85, 1021-1023	3.4	42
265	Self-Assembly Atomic Stacking Transport Layer of 2D Layered Titania for Perovskite Solar Cells with Extended UV Stability. *Advanced Energy Materials*, **2018**, 8, 1701722	21.8	41
264	Wafer-scale and deterministic patterned growth of monolayer MoSvia vapor-liquid-solid method. *Nanoscale*, **2019**, 11, 16122-16129	7.7	40
263	Rational design of a high performance all solid state flexible micro-supercapacitor on paper. *RSC Advances*, **2013**, 3, 15827	3.7	40
262	Complementary-like graphene logic gates controlled by electrostatic doping. *Small*, **2011**, 7, 1552-6	11	40
261	Molecular-packing-enhanced charge transport in organic field-effect transistors based on semiconducting porphyrin crystals. *Applied Physics Letters*, **2007**, 91, 123501	3.4	40
260	Volatile/Nonvolatile Dual-Functional Atom Transistor. *Applied Physics Express*, **2011**, 4, 015204	2.4	39

259	Electron transport in metal/multiwall carbon nanotube/metal structures (metal=Ti or Pt/Au). *Applied Physics Letters*, **2001**, 79, 1354-1356	3.4	39
258	Origin of low-frequency noise in pentacene field-effect transistors. *Solid-State Electronics*, **2011**, 61, 106-110	1.7	38
257	Quantum dots in carbon nanotubes. *Semiconductor Science and Technology*, **2006**, 21, S52-S63	1.8	38
256	Solution-assembled nanowires for high performance flexible and transparent solar-blind photodetectors. *Journal of Materials Chemistry C*, **2015**, 3, 596-600	7.1	37
255	High-performance organic field-effect transistors based on dihexyl-substituted dibenzo[d,d?]thieno[3,2-b;4,5-b?]dithiophene. *Journal of Materials Chemistry*, **2012**, 22, 7715		36
254	Enhanced logic performance with semiconducting bilayer graphene channels. *ACS Nano*, **2011**, 5, 500-6	16.7	36
253	All-Solution-Processed Selective Assembly of Flexible Organic Field-Effect Transistor Arrays. *Applied Physics Express*, **2010**, 3, 051601	2.4	35
252	Spin transport in nanotubes (invited). *Journal of Applied Physics*, **2001**, 89, 6863-6867	2.5	35
251	Reduction of charge injection barrier by 1-nm contact oxide interlayer in organic field effect transistors. *Applied Physics Letters*, **2012**, 100, 013303	3.4	34
250	Interface modification of a pentacene field-effect transistor with a submicron channel. *Applied Physics Letters*, **2006**, 89, 113507	3.4	34
249	Current distribution inside Py□Cu lateral spin-valve devices. *Physical Review B*, **2005**, 71,	3.3	34
248	Patterning technology for solution-processed organic crystal field-effect transistors. *Science and Technology of Advanced Materials*, **2014**, 15, 024203	7.1	33
247	Forming semiconductor/dielectric double layers by one-step spin-coating for enhancing the performance of organic field-effect transistors. *Organic Electronics*, **2012**, 13, 1146-1151	3.5	33
246	Pentacene transistor encapsulated by poly-para-xylylene behaving as gate dielectric insulator and passivation film. *Applied Physics Letters*, **2005**, 87, 183502	3.4	33
245	A search for multiplicity fluctuations in high energy nucleus-nucleus collisions. *Physics Letters, Section B: Nuclear, Elementary Particle and High-Energy Physics*, **1990**, 252, 303-310	4.2	33
244	Gate capacitance in electrochemical transistor of single-walled carbon nanotube. *Applied Physics Letters*, **2006**, 88, 073104	3.4	32
243	In situ purification to eliminate the influence of impurities in solution-processed organic crystals for transistor arrays. *Journal of Materials Chemistry C*, **2013**, 1, 1352-1358	7.1	31
242	Suppression of spin accumulation in nonmagnet due to ferromagnetic ohmic contact. *Applied Physics Letters*, **2004**, 85, 3795-3796	3.4	31

241	Modulation of effective damping constant using spin Hall effect. *Applied Physics Letters*, **2014**, 104, 092408	3.4	30
240	Resistance modulation of multilayer graphene controlled by the gate electric field. *Semiconductor Science and Technology*, **2010**, 25, 034008	1.8	30
239	Solvent-Mediated Shape Engineering of Fullerene (C60) Polyhedral Microcrystals. *Chemistry of Materials*, **2018**, 30, 7146-7153	9.6	30
238	Performance Enhancement of Thin-Film Transistors by Using High-Purity Semiconducting Single-Wall Carbon Nanotubes. *Applied Physics Express*, **2009**, 2, 071601	2.4	29
237	Transition-Voltage Method for Estimating Contact Resistance in Organic Thin-Film Transistors. *IEEE Electron Device Letters*, **2010**, 31, 509-511	4.4	28
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235	Anisotropic transport in graphene on SiC substrate with periodic nanofacets. *Applied Physics Letters* , **2010**, 96, 062111	3.4	27
234	Edge mixing dynamics in graphene p-n junctions in the quantum Hall regime. *Nature Communications*, **2015**, 6, 8066	17.4	26
233	Coulomb blockade in multiwalled carbon nanotube island with nanotube leads. *Applied Physics Letters*, **2001**, 79, 1465-1467	3.4	26
232	Organic light-emitting diode driven by organic thin film transistor on plastic substrates. *Journal of Applied Physics*, **2006**, 99, 064506	2.5	25
231	Charge transport of copper phthalocyanine single-crystal field-effect transistors stable above 100□C. *Applied Physics Letters*, **2006**, 88, 122110	3.4	25
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228	Direct formation of micro-/nanocrystalline 2,5-dimethyl-N,NPdicyanoquinonediimine complexes on SiO2/Si substrates and multiprobe measurement of conduction properties. *Journal of the American Chemical Society*, **2006**, 128, 700-1	16.4	24
227	Pronounced photogating effect in atomically thin WSe2 with a self-limiting surface oxide layer. *Applied Physics Letters*, **2018**, 112, 181902	3.4	23
226	Strain-tunable superconducting field-effect transistor with an organic strongly-correlated electron system. *Advanced Materials*, **2014**, 26, 3490-5	24	23
225	Influence of electrode size on resistance switching effect in nanogap junctions. *Applied Physics Letters*, **2010**, 97, 073118	3.4	23
224	Suppressed pinning field of a trapped domain wall due to direct current injection. *Journal of Applied Physics*, **2003**, 94, 7266-7269	2.5	23

223	On the Mechanism of Commensurability Oscillations in Anisotropic Antidot Lattices. *Journal of the Physical Society of Japan*, **1996**, 65, 811-817	1.5	23
222	Suppression of excess oxygen for environmentally stable amorphous In-Si-O thin-film transistors. *Applied Physics Letters*, **2015**, 106, 192103	3.4	22
221	Self-aligned formation of sub 1 nm gaps utilizing electromigration during metal deposition. *ACS Applied Materials & Interfaces*, **2013**, 5, 12869-75	9.5	22
220	Control of device parameters by active layer thickness in organic field-effect transistors. *Applied Physics Letters*, **2011**, 98, 073307	3.4	22
219	Purification of Single-Wall Carbon Nanotubes Synthesized from Alcohol by Catalytic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2004**, 43, L396-L398	1.4	22
218	Codoping of zinc and tungsten for practical high-performance amorphous indium-based oxide thin film transistors. *Journal of Applied Physics*, **2015**, 118, 125702	2.5	21
217	Effect of air exposure on metal/organic interface in organic field-effect transistors. *Applied Physics Letters*, **2011**, 98, 243301	3.4	21
216	Spin-current-assisted domain-wall depinning in a submicron magnetic wire. *Journal of Applied Physics*, **2003**, 94, 7947	2.5	21
215	Self-powered graphene thermistor. *Nano Energy*, **2016**, 26, 586-594	17.1	21
214	Fullerene/cobalt porphyrin charge-transfer cocrystals: Excellent thermal stability and high mobility. *Nano Research*, **2018**, 11, 1917-1927	10	20
213	Modeling of static electrical properties in organic field-effect transistors. *Journal of Applied Physics*, **2011**, 110, 014510	2.5	20
212	Joule's law for organic transistors exploration: Case of contact resistance. *Journal of Applied Physics* , **2013**, 113, 064507	2.5	19
211	Role of atomic terraces and steps in the electron transport properties of epitaxial graphene grown on SiC. *AIP Advances*, **2012**, 2, 012115	1.5	19
210	Hunting for Monolayer Oxide Nanosheets and Their Architectures. *Scientific Reports*, **2016**, 6, 19402	4.9	18
209	Flexible field-effect transistor arrays with patterned solution-processed organic crystals. *AIP Advances*, **2013**, 3, 052123	1.5	18
208	Extraction of low-frequency noise in contact resistance of organic field-effect transistors. *Applied Physics Letters*, **2010**, 97, 033503	3.4	18
207	Formation mechanism of carbon nanotubes in the gas-phase synthesis from colloidal solutions of nanoparticles. *Current Applied Physics*, **2005**, 5, 128-132	2.6	18
206	Virtual substrate method for nanomaterials characterization. *Nature Communications*, **2017**, 8, 15629	17.4	17

205	Reducing contact resistance in ferroelectric organic transistors by buffering the semiconductor/dielectric interface. *Applied Physics Letters*, **2015**, 107, 053304	3.4	17
204	Controlling the crystal formation in solution-process for organic field-effect transistors with high-performance. *Organic Electronics*, **2012**, 13, 2975-2984	3.5	17
203	Contact resistance instability in pentacene thin film transistors induced by ambient gases. *Applied Physics Letters*, **2009**, 94, 083309	3.4	17
202	Gate-controlled superconducting proximity effect in ultrathin graphite films. *Physica E: Low-Dimensional Systems and Nanostructures*, **2008**, 40, 1495-1497	3	17
201	Growth control of pentacene films on SiO2/Si substrates towards formation of flat conduction layers. *Thin Solid Films*, **2004**, 467, 168-171	2.2	17
200	Temperature-mediated switching of magnetoresistance in Co-contacted multiwall carbon nanotubes. *Applied Physics Letters*, **2003**, 83, 1008-1010	3.4	17
199	Nanoscale Coulomb blockade memory and logic devices. *Nanotechnology*, **2001**, 12, 155-159	3.4	17
198	Spin electronics using carbon nanotubes. *Physica E: Low-Dimensional Systems and Nanostructures*, **2000**, 6, 848-851	3	17
197	On/Off Boundary of Photocatalytic Activity between Single- and Bilayer MoS. *ACS Nano*, **2020**, 14, 6663-6672	16	16
196	Understanding Thickness-Dependent Charge Transport in Pentacene Transistors by Low-Frequency Noise. *IEEE Electron Device Letters*, **2013**, 34, 1298-1300	4.4	16
195	How small the contacts could be optimal for nanoscale organic transistors?. *Organic Electronics*, **2013**, 14, 1797-1804	3.5	16
194	Charge Transport Properties of Hexabenzocoronene Nanotubes by Field Effect: Influence of the Oligoether Side Chains on the Mobility. *Chemistry Letters*, **2009**, 38, 888-889	1.7	16
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191	Scaling effect on the operation stability of short-channel organic single-crystal transistors. *Applied Physics Letters*, **2007**, 91, 063506	3.4	16
190	Reproducible formation of nanoscale-gap electrodes for single-molecule measurements by combination of FIB deposition and tunneling current detection. *Microelectronic Engineering*, **2006**, 83, 1471-1473	2.5	16
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188	Influence of edge current and contact on nonlocal Shubnikov-de Haas oscillations in macroscopic GaAs/AlGaAs wire. *Solid State Communications*, **1991**, 80, 571-574	1.6	16

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186	Gate-Controlled PIN Junction Switching Device with Graphene Nanoribbon. *Applied Physics Express*, **2012**, 5, 015101	2.4	15
185	Tunable contact resistance in double-gate organic field-effect transistors. *Organic Electronics*, **2012**, 13, 1583-1588	3.5	15
184	Effect of probe configuration on spin accumulation in lateral spin-valve structure. *Journal of Magnetism and Magnetic Materials*, **2005**, 286, 88-90	2.8	15
183	Charge transfer control by gate voltage in crossed nanotube junction. *Applied Physics Letters*, **2002**, 81, 2250-2252	3.4	15
182	Transport properties in artificial lateral superlattice. *Superlattices and Microstructures*, **1994**, 16, 295-301	2.8	15
181	Tunable Doping of Rhenium and Vanadium into Transition Metal Dichalcogenides for Two-Dimensional Electronics. *Advanced Science*, **2021**, 8, e2004438	13.6	15
180	High-performance non-volatile field-effect transistor memories using an amorphous oxide semiconductor and ferroelectric polymer. *Journal of Materials Chemistry C*, **2016**, 4, 7917-7923	7.1	14
179	Liquid phase growth of graphene on silicon carbide. *Carbon*, **2012**, 50, 5076-5084	10.4	14
178	Power transfer-length method for full biasing contact resistance evaluation of organic field-effect transistors. *Organic Electronics*, **2011**, 12, 2019-2024	3.5	14
177	Dependence of proximity-induced supercurrent on junction length in multilayer-graphene Josephson junctions. *Physica C: Superconductivity and Its Applications*, **2010**, 470, 1477-1480	1.3	14
176	Fabrication of ultrashort graphene Josephson junctions. *Physica C: Superconductivity and Its Applications*, **2010**, 470, 1492-1495	1.3	14
175	Coulomb Blockade Oscillations in Narrow Corrugated Graphite Ribbons. *Applied Physics Express*, **2008**, 1, 024001	2.4	14
174	Nonlocal quantum conduction and the influence of contact resistance in GaAs/AlGaAs wires. *Surface Science*, **1992**, 267, 282-285	1.8	14
173	Unravelling the origin of the photocarrier dynamics of fullerene-derivative passivation of SnO2 electron transporters in perovskite solar cells. *Journal of Materials Chemistry A*, **2020**, 8, 23607-23616	13	14
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171	Identifying the molecular adsorption site of a single molecule junction through combined Raman and conductance studies. *Chemical Science*, **2019**, 10, 6261-6269	9.4	13
170	Large [6,6]-phenyl C61 butyric acid methyl (PCBM) hexagonal crystals grown by solvent-vapor annealing. *Materials Chemistry and Physics*, **2014**, 145, 327-333	4.4	13

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